Micron Semiconductor Ltd.

Date: 05.11.2013
Design Type: MSX25-500
Customer: Aarhus University
Purchase Order Number: 060551

Measurement Data in Air @ 20°C:

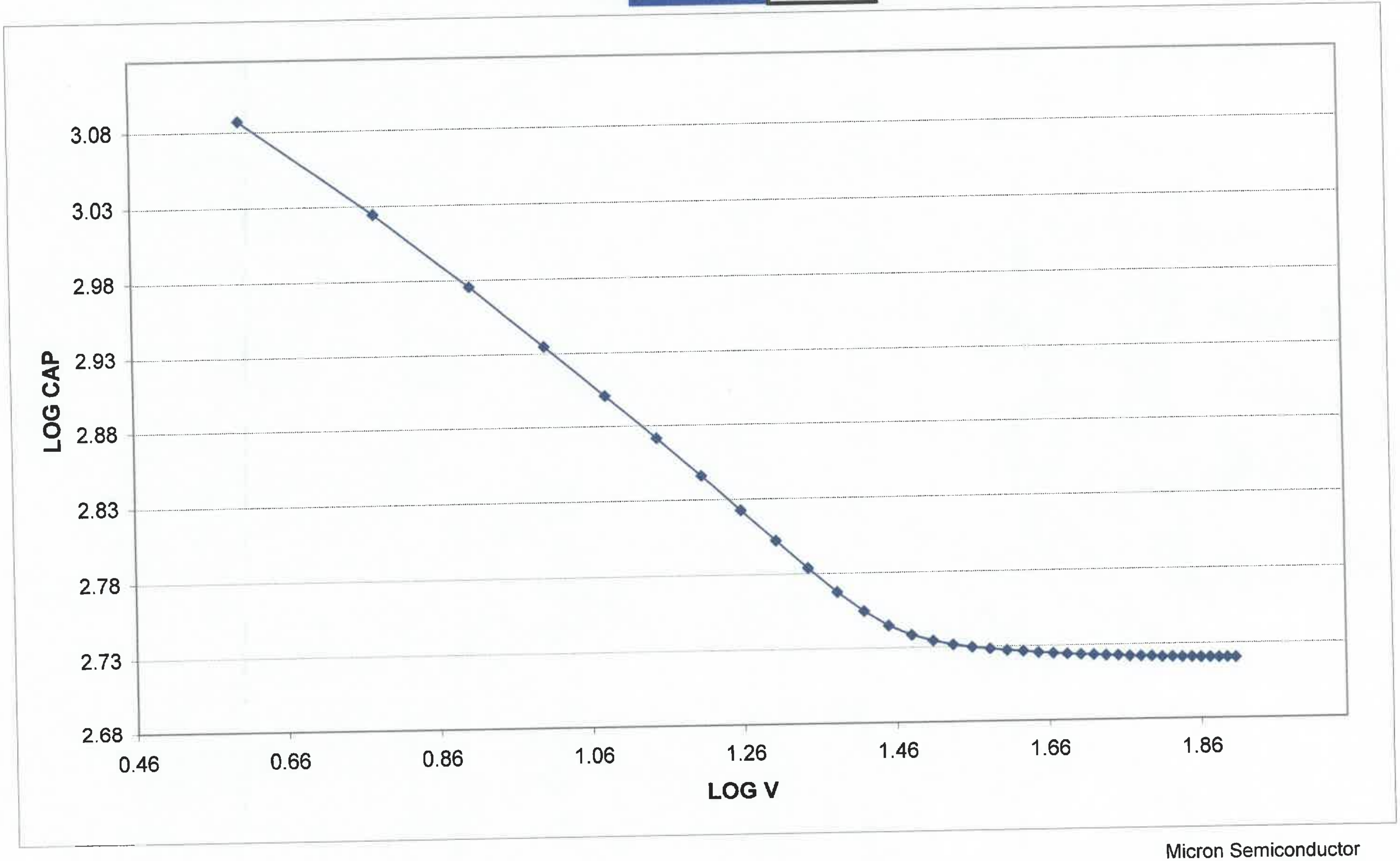
Device Number	Thickness	Depletion Voltage	IR @ Dep.	IR @ Dep.+30V	Vb @ 10uA	Vf @ 10mA
2826-7	524uM	36V	92nA	96nA	>100V	0.58V

Depletion Plot MSX25-500

Wafer No.: 2826-7

Thickness: 524 um

Depletion: 36 Volts



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31-08-12

Resolution Plot

MSX25-500

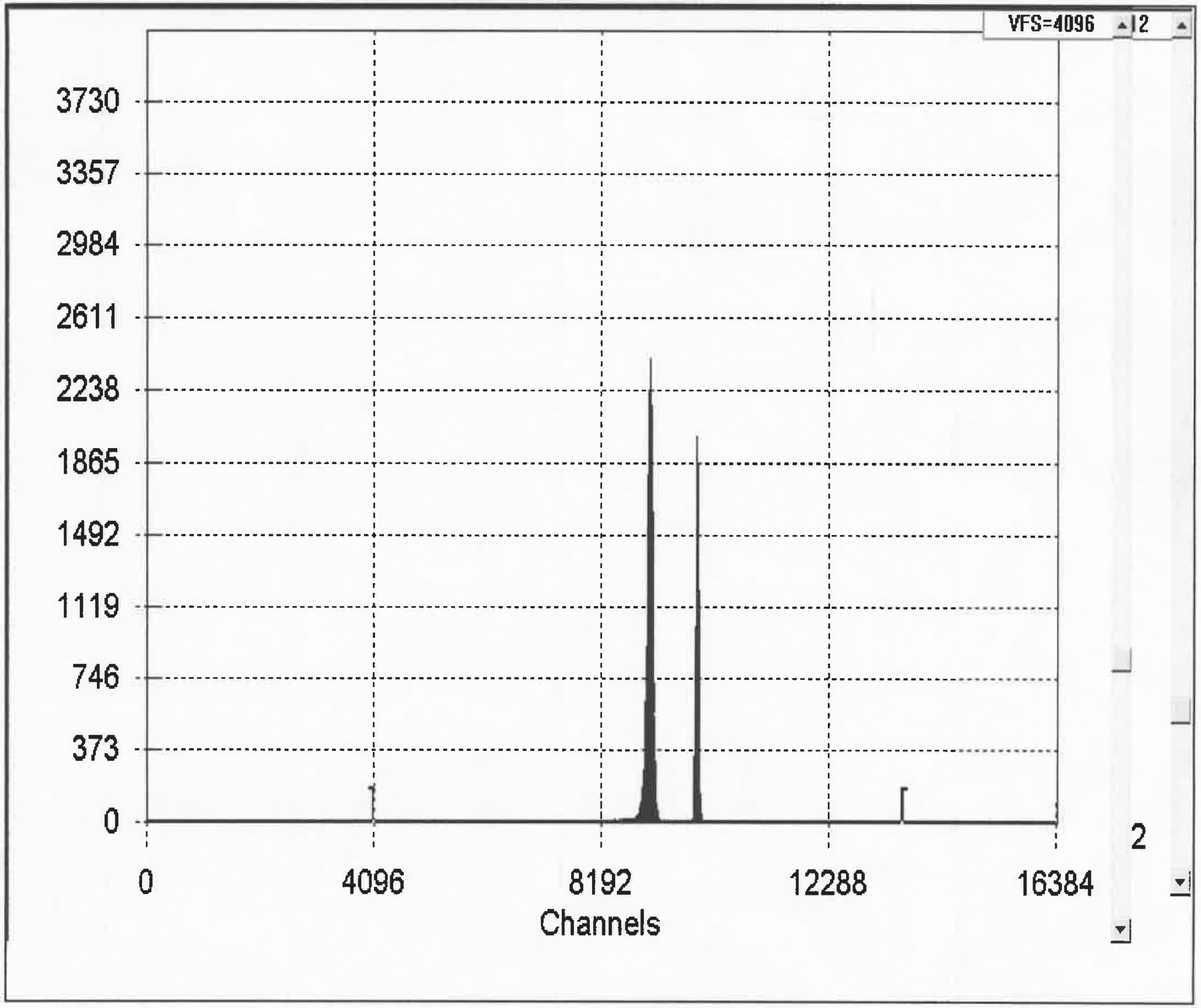
Wafer No.: 2826-7 **Thickness:** 524 um

JUNCTION

DET LINE: 77.2 KeV
SYSTEM: 44.1 KeV
CAL: 63.4 KeV

OHMIC

DET LINE: 78.1 KeV
SYSTEM: 44.2 KeV
CALC: 64.4 KeV



Source
Am 241

Rise Time
1

Flat Top
0

BIAS VOLTS= 60 V

Leakage 173 nA

Micron Semiconductor
27/09/2012